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Kunihiro Hosono
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Banqiu Wu, Applied Materials, Inc. (United States)

EUV Mask II

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Nano Imprint and Patterned Media

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Process and Repair

Toshio Konishi, Toppan Printing Company, Ltd. (Japan)

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Mask-related Lithography

Minoru Sugawara, Sony Corporation (Japan)

Steffen Schulze, Mentor Graphics Corporation (United States)

EDA, DFM, and MDP

Kokoro Kato, SII NanoTechnology Inc. (Japan)

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